

High Speed Infrared Emitting Diode, 850 nm, Surface Emitter Technology



FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm): $\varnothing$ 5
- Leads with stand-off
- Peak wavelength: $\lambda_p = 850$ nm
- High reliability
- High radiant power
- High radiant intensity
- Narrow angle of half intensity: $\phi = \pm 3^\circ$
- Suitable for high pulse current operation
- Good spectral matching with CMOS cameras
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition



RoHS
COMPLIANT
GREEN
(5-2008)**

DESCRIPTION

VSLY5850 is an infrared, 850 nm emitting diode based on GaAlAs surface emitter chip technology with extreme high radiant intensity, high optical power and high speed, molded in a clear, untinted plastic package, with a parabolic lens.

APPLICATIONS

- Infrared radiation source for operation with CMOS cameras
- High speed IR data transmission
- Smoke-automatic fire detectors
- IR Flash

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	ϕ (deg)	λ_p (nm)	t_r (ns)
VSLY5850	600	± 3	850	10

Note

- Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
VSLY5850	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$

Note

- MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5$, $t_p = 100 \mu\text{s}$	I_{FM}	200	mA
Surge forward current	$t_p = 100 \mu\text{s}$	I_{FSM}	1	A
Power dissipation		P_V	190	mW
Junction temperature		T_j	100	$^\circ\text{C}$
Operating temperature range		T_{amb}	- 40 to + 85	$^\circ\text{C}$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ\text{C}$
Soldering temperature	$t \leq 5$ s, 2 mm from case	T_{sd}	260	$^\circ\text{C}$
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R_{thJA}	230	K/W

** Please see document "Vishay Material Category Policy": www.vishay.com/doc?99902

Vishay Semiconductors

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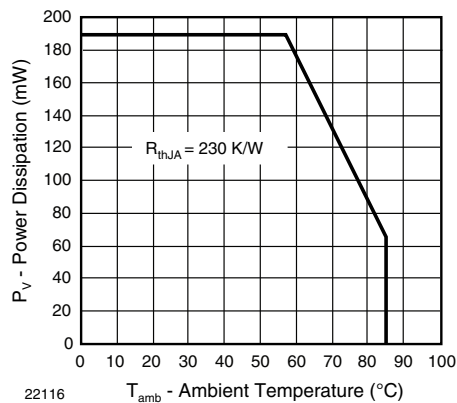


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

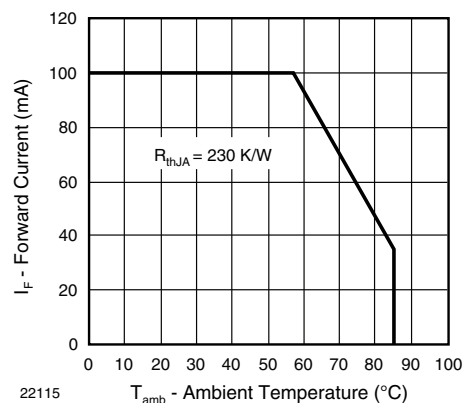


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	V_F		1.65	1.9	V
	$I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	V_F		2.9		V
Temperature coefficient of V_F	$I_F = 1\text{ mA}$	TK_{VF}		- 1.45		mV/K
	$I_F = 10\text{ mA}$	TK_{VF}		- 1.25		mV/K
Reverse current		I_R	not designed for reverse operation			μA
Junction capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$	C_j		125		pF
Radiant intensity	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	I_e	300	600	900	mW/sr
	$I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	I_e		5100		mW/sr
Radiant power	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	ϕ_e		55		mW
Temperature coefficient of ϕ_e	$I_F = 100\text{ mA}$	TK_{ϕ_e}		- 0.35		%/K
Angle of half intensity		ϕ		± 3		deg
Peak wavelength	$I_F = 100\text{ mA}$	λ_p	840	850	870	nm
Spectral bandwidth	$I_F = 100\text{ mA}$	$\Delta\lambda$		30		nm
Temperature coefficient of λ_p	$I_F = 100\text{ mA}$	TK_{λ_p}		0.25		nm/K
Rise time	$I_F = 100\text{ mA}$	t_r		10		ns
Fall time	$I_F = 100\text{ mA}$	t_f		10		ns

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

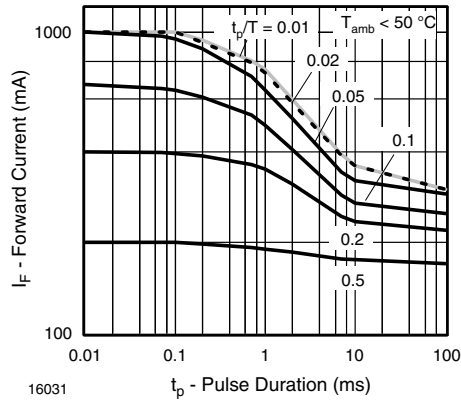


Fig. 3 - Pulse Forward Current vs. Pulse Duration

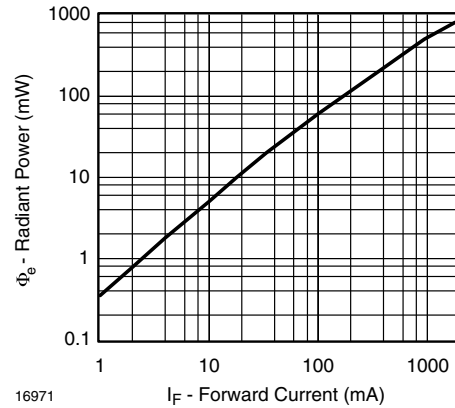


Fig. 6 - Radiant Power vs. Forward Current

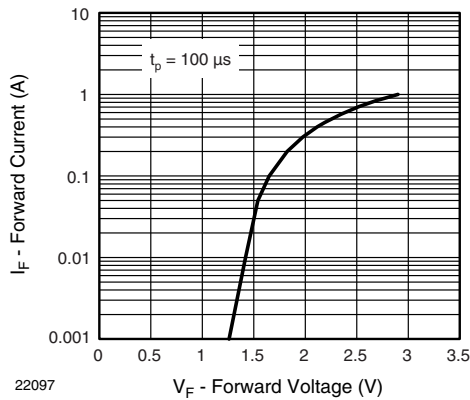


Fig. 4 - Forward Current vs. Forward Voltage

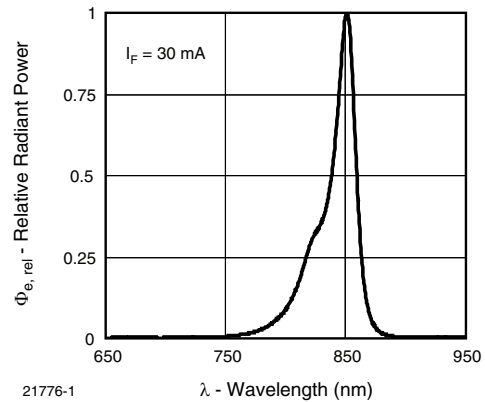


Fig. 7 - Relative Radiant Power vs. Wavelength

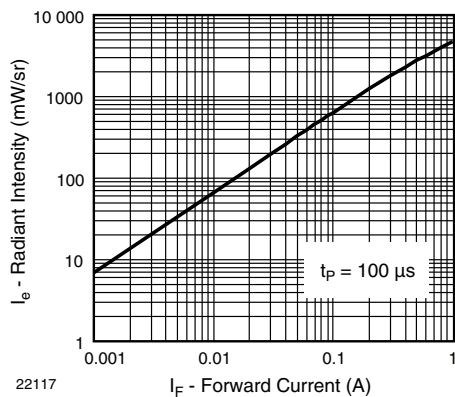


Fig. 5 - Radiant Intensity vs. Forward Current

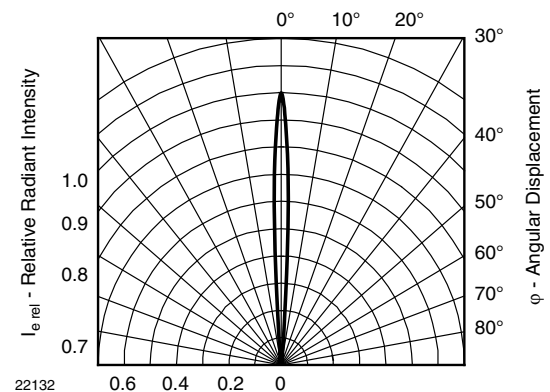
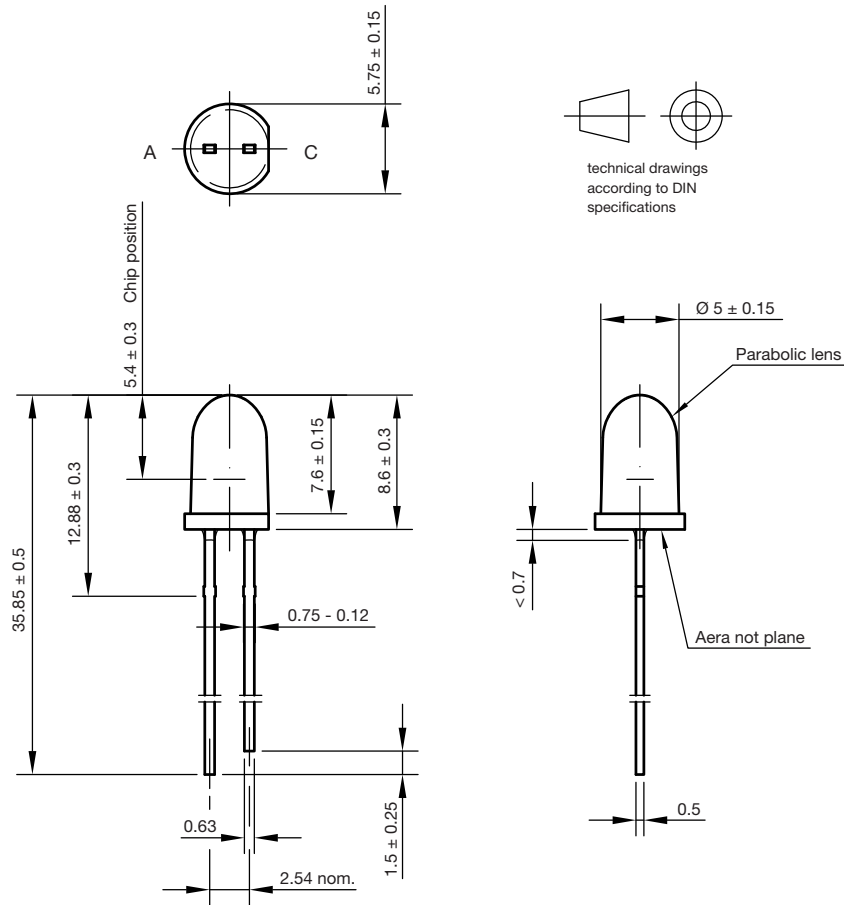


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



technical drawings
according to DIN
specifications

Drawing-No.: 6.544-5385.01-4
Issue: 2; 08.03.10
20531

Not indicated tolerances ± 0.1

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